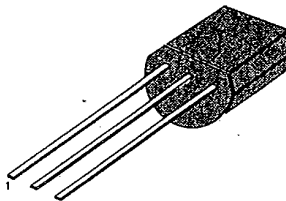


KSK30**SILICON N-CHANNEL JUNCTION FET****LOW NOISE PRE-AMP. USE**High Input Impedance: $I_{gss} = 1\text{nA}$ (MAX)Low Noise: $NF = 0.5\text{dB}$ (TYP)High Voltage: $V_{gds} = -50\text{V}$ **ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)**

Characteristic	Symbol	Rating	Unit
Gate-Drain Voltage	V_{gds}	-50	V
Gate Current	I_g	10	mA
Collector Dissipation	P_c	100	mW
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~125	$^\circ\text{C}$

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1. Source 2. Gate 3. Drain

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Gate-Drain Breakdown Voltage	BV_{gds}	$V_{DS} = 0, I_g = -100\mu\text{A}$	-50			V
Gate Leak Current	I_{gss}	$V_{gs} = -30\text{V}, V_{DS} = 0$			-1	nA
Drain Leak Current	I_{DSS}	$V_{DS} = 10\text{V}, V_{GS} = 0$	0.3		6.5	mA
Gate-Source Voltage	$V_{gs(off)}$	$V_{DS} = 10\text{V}, I_D = 0.1\mu\text{A}$	-0.4		-5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}, V_{GS} = 0, f = 1\text{KHz}$	1.2			mS
Input Capacitance	C_{iss}	$V_{DS} = 0, V_{GS} = 0, f = 1\text{MHz}$		8.2		pF
Feedback Capacitance	C_{rss}	$V_{gd} = -10\text{V}, V_{DS} = 0$ $f = 1\text{MHz}$		2.6		pF
Noise Figure	NF	$V_{DS} = 15\text{V}, V_{GS} = 0$ $R_g = 100\text{k}\Omega$ $f = 120\text{Hz}$		0.5	5	dB

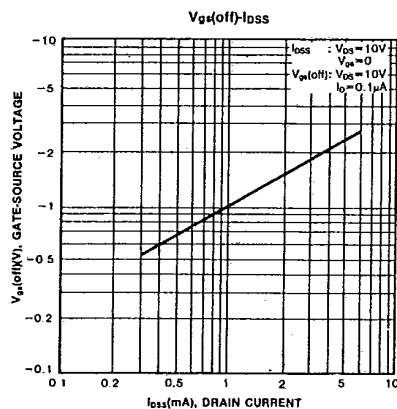
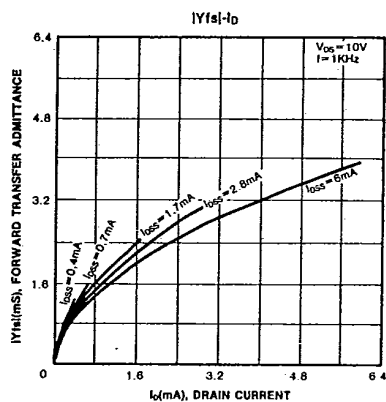
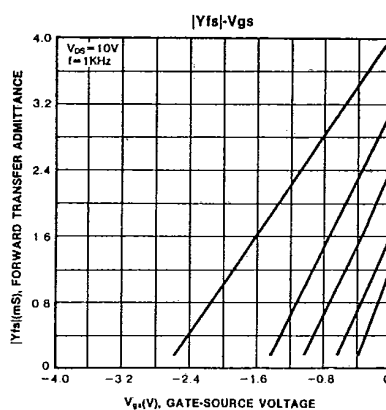
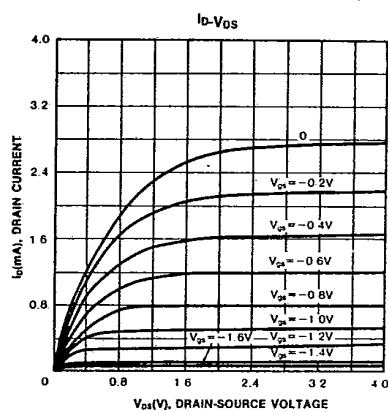
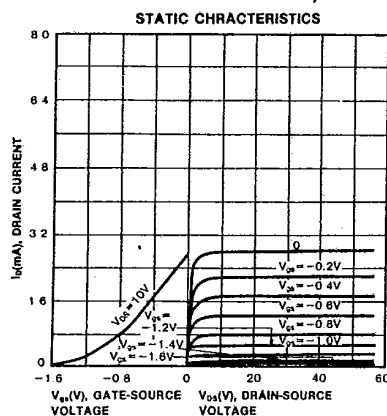
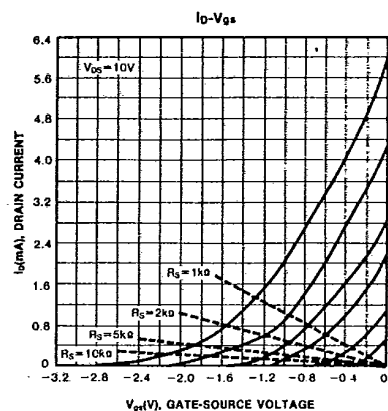
 I_{DSS} CLASSIFICATION

Classification	R	O	Y	G
$I_{DSS}(\text{mA})$	0.30-0.75	0.60-1.40	1.20-3.00	2.60-6.50



KSK30**SILICON N-CHANNEL JUNCTION FET**

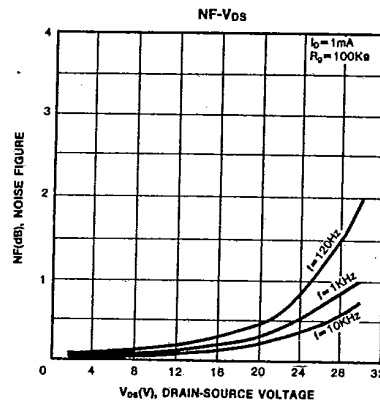
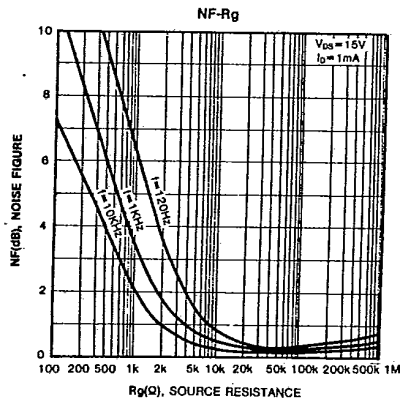
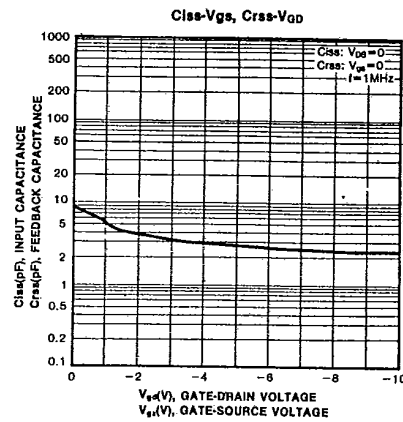
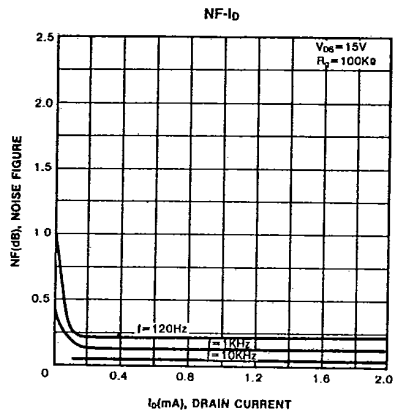
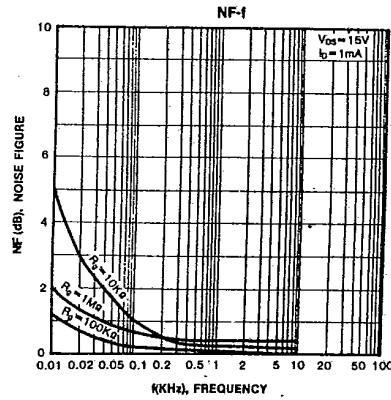
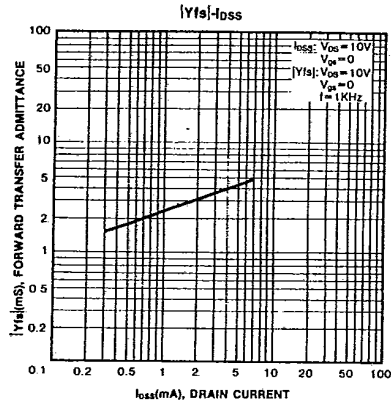
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